

N-channel TrenchMOS standard level FET 28 July 2016

Product data sheet

1. General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	58	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	96	W
Static charact	eristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 11		-	9.44	13	mΩ
Dynamic char	acteristics		1				
Q _{GD}	gate-drain charge	I _D = 15 A; V _{DS} = 48 V; V _{GS} = 10 V; Fig. 13; Fig. 14		-	6.9	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UF4
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK7613-60E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7613-60E	BUK7613-60E

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	60	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	60	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC	-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	96	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u>	-	58	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 2</u>	-	41	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3	-	234	А
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
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BUK7613-60E

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Symbol	Parameter	Conditions		Min	Мах	Unit	
Source-drain	Source-drain diode					_	
I _S	source current	T _{mb} = 25 °C	[1]	-	58	А	
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	234	А	
Avalanche rug	Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 58 \text{ A}; \text{V}_{\text{sup}} \leq 60 \text{V}; \text{R}_{\text{GS}} = 50 \Omega; \\ \text{V}_{\text{GS}} &= 60 \text{V}; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ \hline \text{Fig. 4} \end{split}$	[<u>2][3]</u>	-	37	mJ	

[1]

Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [2]

Refer to application note AN10273 for further information. [3]

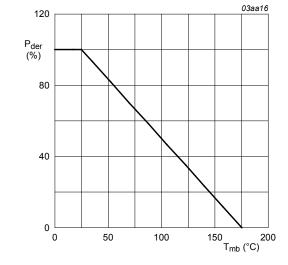


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

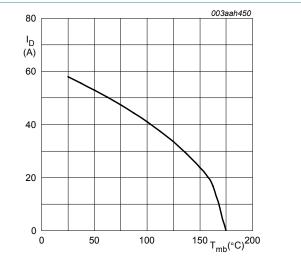
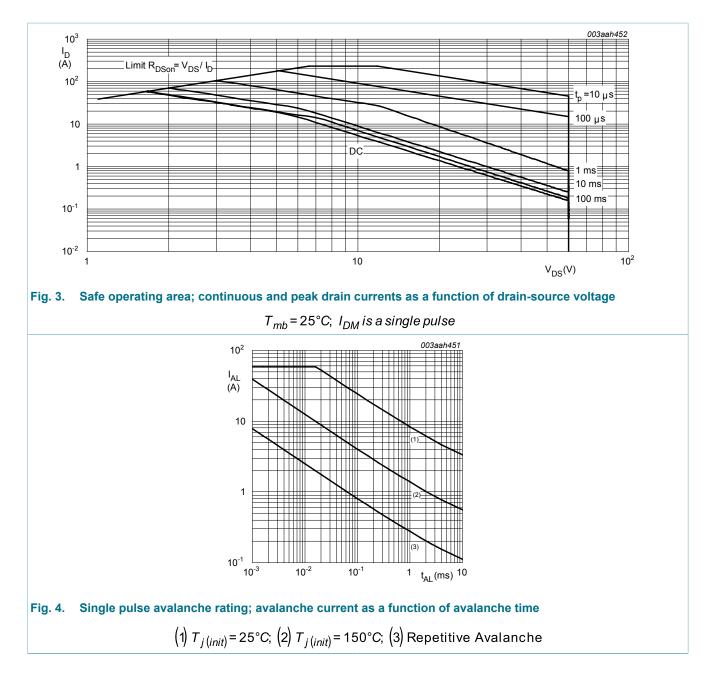


Fig. 2. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$

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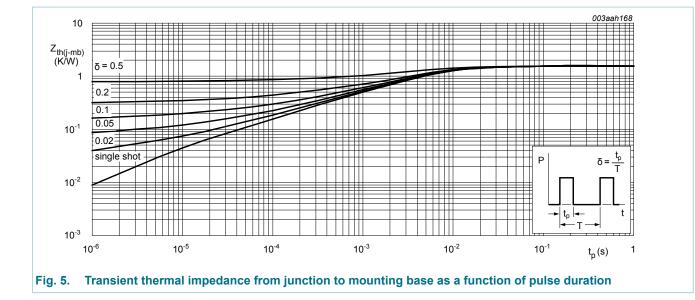
9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	1.56	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

Table 6. Thermal characteristics

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · ·				
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	54	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	1	-	-	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	4.5	V	
I _{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	0.025	1	μA
		V_{DS} = 60 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	ss gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon} drain-source on-state resistance		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	9.44	13	mΩ
	V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	28.2	mΩ	
Dynamic ch	naracteristics	· · · · ·	ł	- 1		
Q _{G(tot)}	total gate charge	I _D = 15 A; V _{DS} = 48 V; V _{GS} = 10 V;	-	22.9	-	nC
Q _{GS}	gate-source charge	<u>Fig. 13; Fig. 14</u>	-	5	-	nC
Q _{GD}	gate-drain charge		-	6.9	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	1298	1730	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	197	237	pF
C _{rss}	reverse transfer capacitance		-	122	162	pF
t _{d(on)}	turn-on delay time	V_{DS} = 45 V; R _L = 3 Ω; V _{GS} = 10 V; R _{G(ext)} = 5 Ω	-	10.8	-	ns
t _r	rise time		-	9.2	-	ns
t _{d(off)}	turn-off delay time		-	21.9	-	ns
t _f	fall time		-	9.8	-	ns
L _D	internal drain inductance	from upper edge of mounting base to centre of die	-	2.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad	-	7.5	-	nH
Source-dra	in diode	· · · ·		1		
V _{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 16</u>	-	0.84	1.2	V
t _{rr}	reverse recovery time	I_{S} = 15 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	21.3	-	ns
Q _r	recovered charge	V _{DS} = 25 V	-	18.1	-	nC

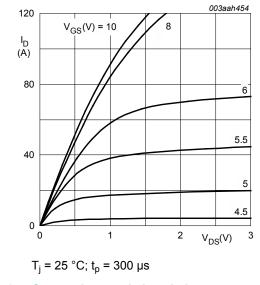
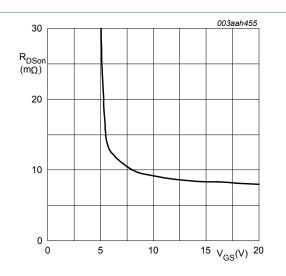


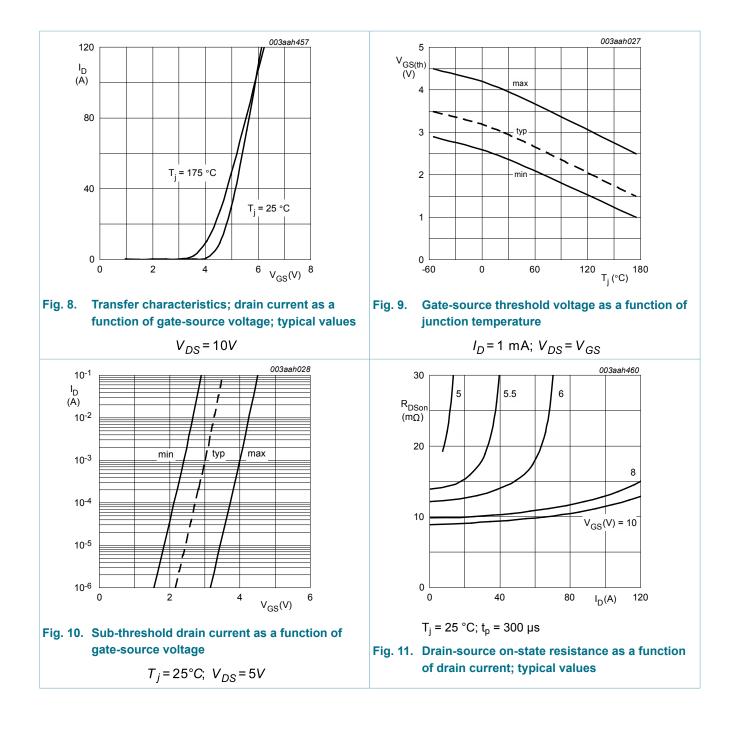
Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values





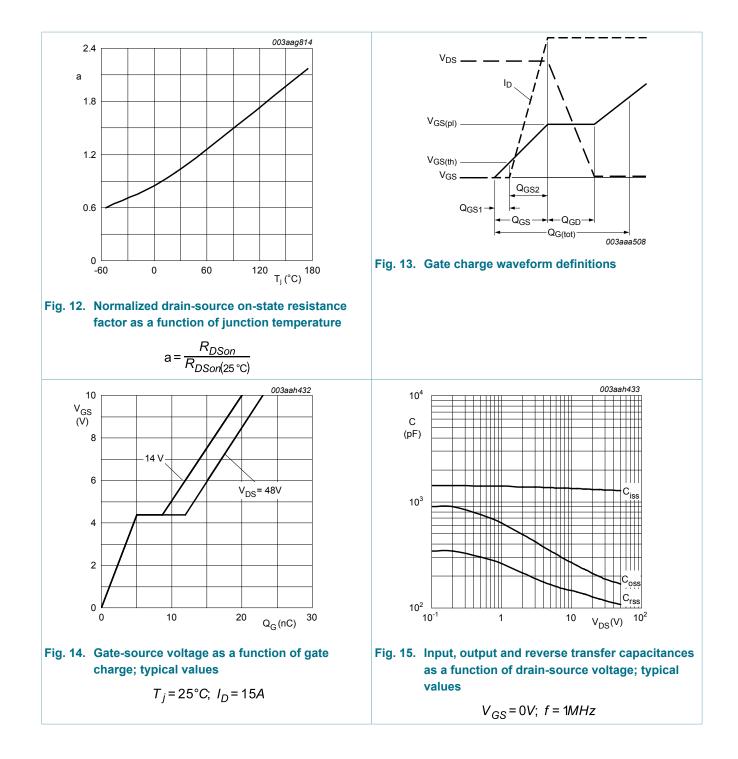
 $T_j = 25^{\circ}C; I_D = 15A$

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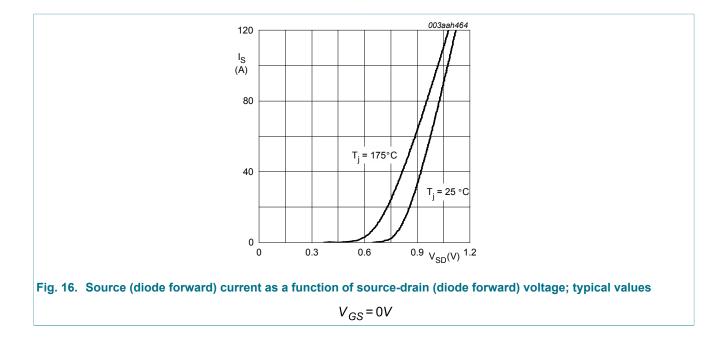
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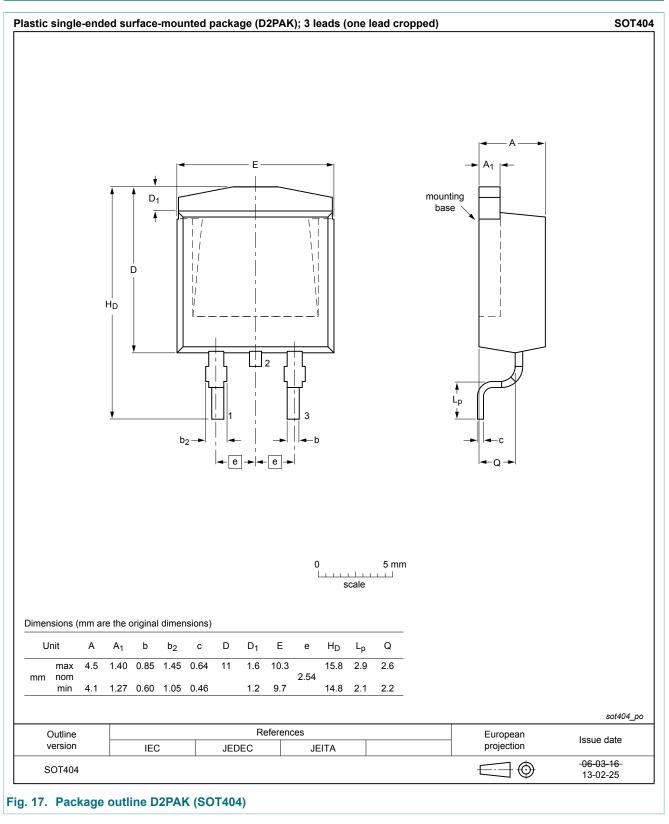
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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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